



30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BVDSS	R _{DS(ON)} Max	I _D Max Tc = +25°C
	1.6mΩ @ V _{GS} = 10V	120A
30V	$2.6\text{m}\Omega$ @ $V_{GS} = 4.5V$	97A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power-management applications.

- Backlighting
- Power-management functions
- DC-DC converters

Features and Benefits

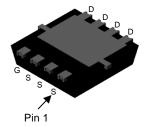
- Low R_{DS(ON)} Ensures On-State Losses Are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspection
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

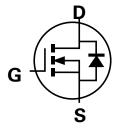
Mechanical Data

- Package: PowerDI[®]3333-8
- Package Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208(3)
- Weight: 0.03 grams (Approximate)

PowerDI3333-8/SWP (Type UX)







Top View

Bottom View

Equivalent Circuit

Ordering Information (Note 4)

Orderable Part Number	Paakaga	Packing		
Orderable Part Number	Package	Qty.	Carrier	
DMT31M4LFVW-7	PowerDI3333-8/SWP (Type UX)	2000	Tape & Reel	
DMT31M4LFVW-13	PowerDI3333-8/SWP (Type UX)	3000	Tape & Reel	

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



3M4 = Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 25 = 2025)

WW = Week Code (01 to 53)

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Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	30	V	
Gate-Source Voltage	V _{GSS}	±20	V	
Continuous Drain Current, $V_{GS} = 10V$ (Note 5) $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		lο	34 27	А
Continuous Drain Current, $V_{GS} = 10V$ (Note 6) $T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$		lo	120 96	А
Maximum Continuous Body Diode Forward Current (Note 5)	Is	3.5	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	448	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	Ism	448	Α	
Avalanche Current, L = 0.1mH	I _{AS}	50	Α	
Avalanche Energy, L = 0.1mH	Eas	128	mJ	

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T _A = +25°C	PD	3.2	W
Thermal Resistance, Junction to Ambient (Note 5) Steady State		$R_{ heta JA}$	38.4	°C/W
Total Power Dissipation (Note 7) TA = +2		PD	1.4	W
Thermal Resistance, Junction to Ambient (Note 7) Steady State		$R_{\theta JA}$	90.6	°C/W
Thermal Resistance, Junction to Case (Note 6) Steady State		R _θ JC	3.06	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

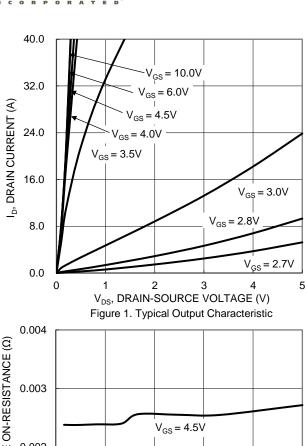
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

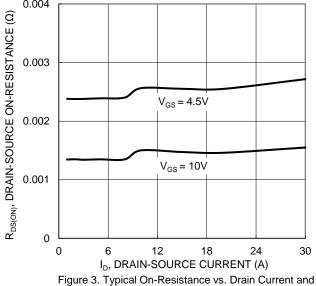
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	_	_	V	$V_{GS} = 0$, $I_{D} = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 24V, V_{GS} = 0$	
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	Vgs(TH)	1.2		2.5	V	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
Static Drain-Source On-Resistance	D	_	1.1	1.6	mΩ	V _G S = 10V, I _D = 30A	
Static Drain-Source On-Resistance	RDS(ON)	_	2.3	2.6		$V_{GS} = 4.5V, I_D = 30A$	
Diode Forward Voltage	VsD	_	0.7	1.2	V	V _G S = 0, I _S = 1A	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	Ciss	_	2955	_	pF		
Output Capacitance	Coss	_	899	_	pF	$V_{DS} = 15V, V_{GS} = 0,$ f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	_	54	_	pF	T = 1.0WHZ	
Gate Resistance	Rg	_	1.51	_	Ω	$V_{DS} = 0$, $V_{GS} = 0$, $f = 1.0MHz$	
Total Gate Charge (Vgs = 4.5V)	Qg	_	18.2	_	nC		
Total Gate Charge (Vgs = 10V)	Qg	_	37.3	_	nC	V _{DS} = 15V, V _{GS} = 4.5V,	
Gate-Source Charge	Qgs	_	7.8	_	nC	I _D = 10A	
Gate-Drain Charge	Qgd	_	4.1	_	nC	1	
Turn-On Delay Time	t _{D(ON)}	_	4.5	_	ns		
Turn-On Rise Time	t _R	_	12	_	ns	V _{GS} = 10V, V _{DD} = 15V,	
Turn-Off Delay Time	tD(OFF)	_	22.9	_	ns	$R_{G} = 3.3\Omega, I_{D} = 10A$	
Turn-Off Fall Time	t _F	_	12	_	ns		

Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
- 6. Thermal resistance from junction to soldering point (on the exposed drain pad).
- 7. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
- 8. Short duration pulse test used to minimize self-heating effect.
- 9. Guaranteed by design. Not subject to product testing.







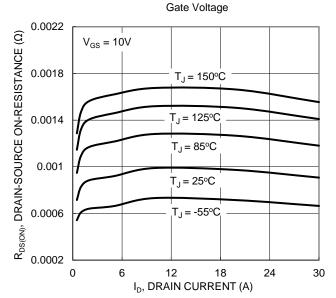
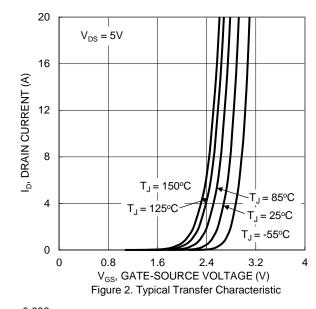
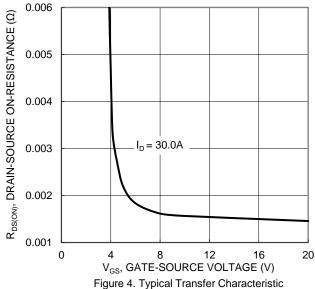


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature





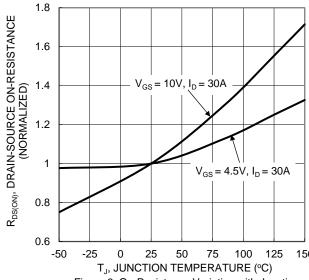


Figure 6. On-Resistance Variation with Junction Temperature



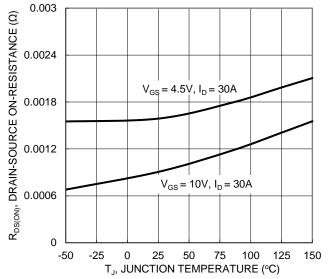


Figure 7. On-Resistance Variation with Junction

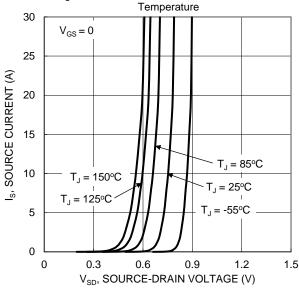


Figure 9. Diode Forward Voltage vs. Current

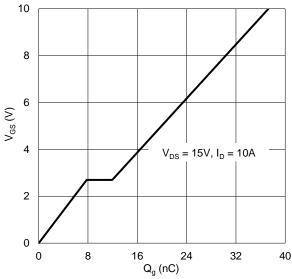


Figure 11. Gate Charge

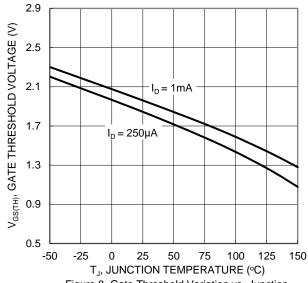
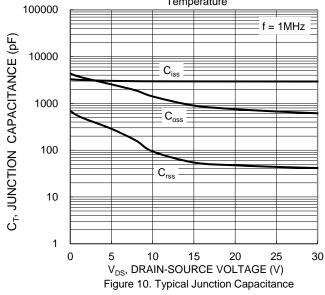
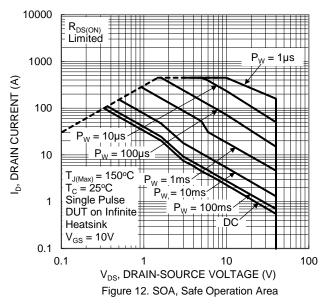


Figure 8. Gate Threshold Variation vs. Junction Temperature







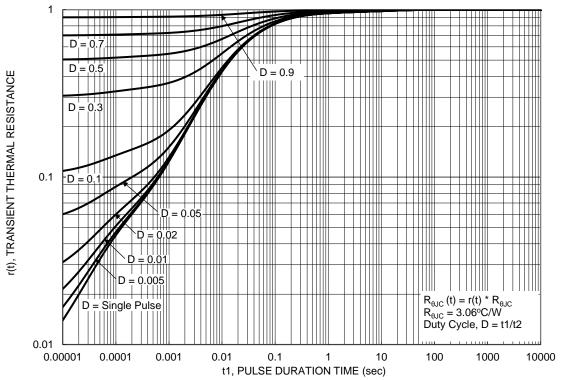


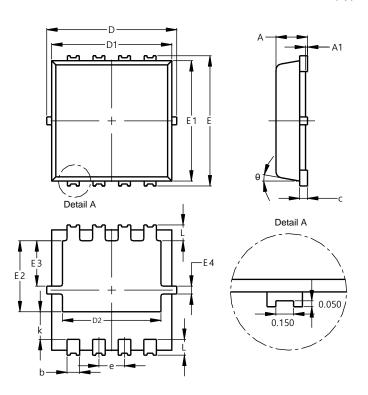
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)

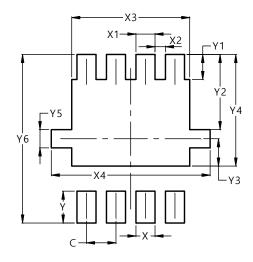


PowerDI3333-8/SWP					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	-		
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е			0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)		
C	0.650		
X	0.420		
X1	0.420		
X2	0.230		
Х3	2.600		
X4	3.500		
Y	0.700		
Y1	0.550		
Y2	1.650		
Y3	0.600		
Y4	2.450		
Y5	0.400		
Y6	3.700		



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